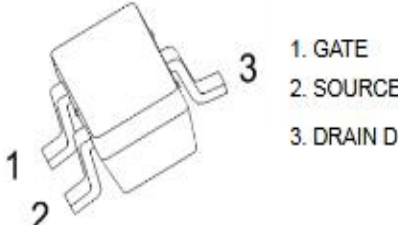
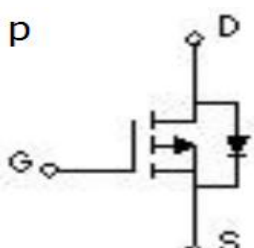

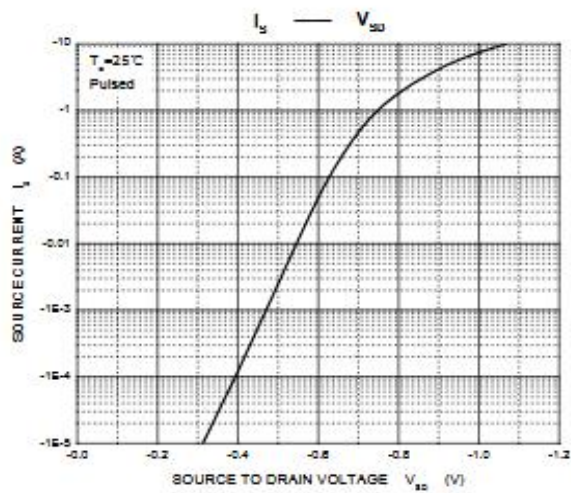
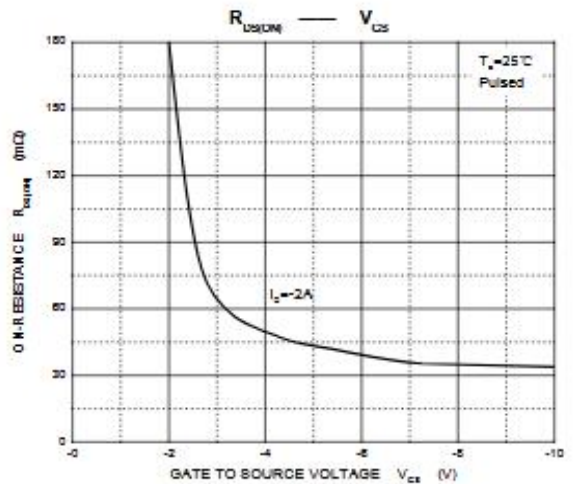
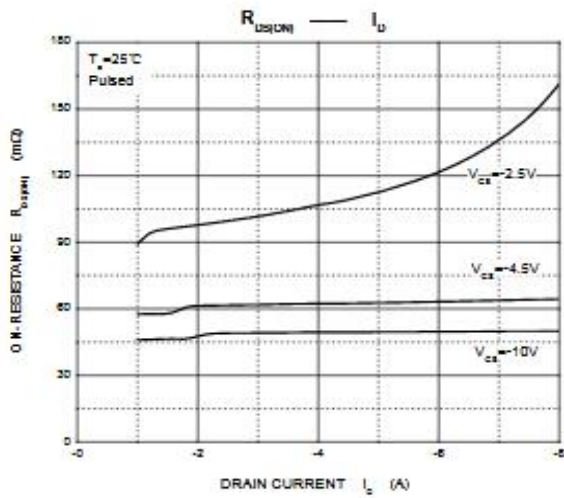
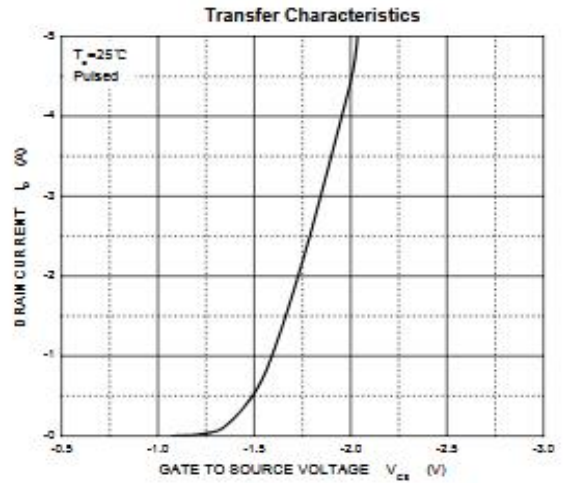
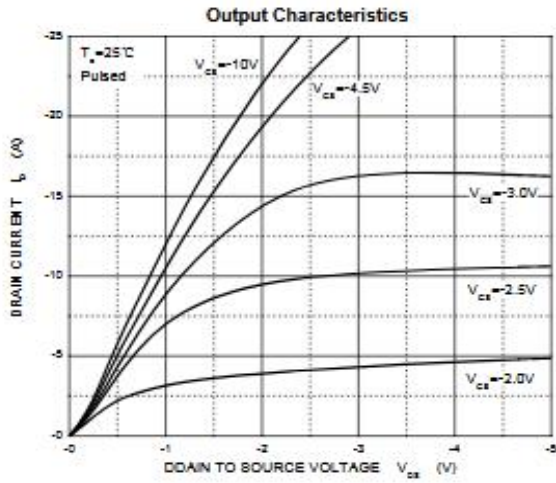


P-Channel 30-V(D-S) MOSFET		SOT-23-3L Plastic-Encapsulate MOSFETS	
<p style="text-align: center;"><u>SOT-23-3L</u></p>  <p style="text-align: center;"><b>Equivalent Circuit</b></p> 		<p><b>Features</b></p> <ul style="list-style-type: none"> <li>※ TrenchFET Power MOSFET</li> </ul> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>※ Load Switch for Portable Devices</li> <li>※ DC/DC Converter</li> </ul> <p><b>MARKING</b></p> 	
<b>V(BR)DSS</b>	<b>RDS(on)MAX</b>		<b>ID</b>
-30 V	60m Ω @-10V		-4. 1A
	68m Ω @-4.5V		
	90m Ω @-2.5V		
<b>Maximum ratings ( Ta=25°C unless otherwise noted)</b>			
<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Drain-Source Voltage	VDS	-30	V
Gate-Source Voltage	VGS	±12	
Continuous Drain Current	ID	-4. 1	A
Pulsed Diode Curren	IDM	-15	
Continuous Source-Drain Current(Diode Conduction)	IS	-0. 8	
Power Dissipation	PD	0. 35	W
Thermal Resistance from Junction to Ambient (t≤5s)	R θ JA	150	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	°C

<b>MOSFET ELECTRICAL CHARACTERISTICS</b>						
<b>Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)</b>						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250μA	-30			V
Gate-source threshold voltage	VGS(th)	VDS = VGS, ID = -250μA	-0.6	-0.87	-1.2	V
Gate-source leakage	IGSS	VDS = 0V, VGS = ±12V		2.1/-0.76	±100	nA
Zero gate voltage drain current	IDSS	VDS = -30V, VGS = 0V			-1	μA
Drain-source on-state resistancea	RDS(on)	VGS = -10V, ID = -0.5A		47.35	60	mΩ
		VGS = -4.5V, ID = -0.5A		60.06	68	mΩ
		VGS = -2.5V, ID = -0.5A		82.17	90	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -4A	7			S
Diode forward voltage	VSD	IS=-1A, VGS=0V	-0.5	-0.8	-1	V
<b>Dynamic</b>						
Input capacitance	Ciss	VDS = 15V, VGS = 0V, f=1MHz			1050	pF
Output capacitance	Coss			99		pF
Reverse transfer capacitanceb	Crss			77		pF
Total gate charge	Qg	VDS = -10V, VGS = -4.5V, ID = -4.5A		11	14	nC
Gate-source charge	Qgs			1.3		nC
Gate-drain charge	Qgd			2.8		nC
Gate resistance	Rg	f=1MHz			3.6	Ω
<b>Switchingb</b>						
Turn-on delay time	td(on)	VDD= -10V RL=10Ω, ID ≈ 1-A, VGEN= -4.5V, Rg=6Ω		7	15	ns
Rise time	tr			15	20	ns
Turn-off delay time	td(off)			38	50	ns
Fall time	tf			3	10	ns
<b>Drain-source body diode characteristics</b>						
Continuous Source-Drain Diode Current	IS	Tc=25°C			-1.3	A
Pulsed Diode forward Current	ISM				-20	A
<b>Note :</b>						
1. Repetitive Rating : Pulse width limited by maximum junction temperature.						
2. Surface Mounted on FR4 Board, t < 5 sec.						
3. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.						
4. Guaranteed by design, not subject to production testing.						

**Typical Characteristics:**



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)